RAPID COMMUNICATION

A reversible surface functionalized nanowire transistor to study protein—protein interactions

Shu-Ping Lin\textsuperscript{a,b,1}, Chien-Yuan Pan\textsuperscript{c,1}, Kun-Chang Tseng\textsuperscript{b}, Ming-Chou Lin\textsuperscript{d,e}, Chii-Dong Chen\textsuperscript{d,f}, Chia-Chang Tsai\textsuperscript{a,b}, Shu-Han Yu\textsuperscript{a,g}, Ying-Chieh Sun\textsuperscript{g}, Tsung-Wu Lin\textsuperscript{a,b}, Yit-Tsong Chen\textsuperscript{a,b,*}

\textsuperscript{a} Institute of Atomic and Molecular Sciences, Academia Sinica, P.O. Box 23-166, Taipei 106, Taiwan
\textsuperscript{b} Department of Chemistry, National Taiwan University, No. 1, Sec. 4, Roosevelt Road, Taipei 106, Taiwan
\textsuperscript{c} Institute of Zoology and Department of Life Science, National Taiwan University, No. 1, Sec. 4, Roosevelt Road, Taipei 106, Taiwan
\textsuperscript{d} Institute of Physics, Academia Sinica, Taipei 115, Taiwan
\textsuperscript{e} Graduate Institute of Electronics Engineering and Department of Electrical Engineering, National Taiwan University, No. 1, Sec. 4, Roosevelt Road, Taipei 106, Taiwan
\textsuperscript{f} Department of Physics, National Cheng Kung University, Tainan 701, Taiwan
\textsuperscript{g} Department of Chemistry, National Taiwan Normal University, No. 88, Sec. 4, Ting Chow Road, Taipei 116, Taiwan

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KEYWORDS
Nanowire; Field-effect transistor; Reversible surface functionalization; Protein—protein interaction

Summary Taking advantage of the reversible association—dissociation between glutathione (GSH) and glutathione S-transferase (GST), we have developed a novel method by surface-functionalizing GSH on silicon nanowire field-effect transistors (SiNW-FET) and then anchoring a particular GST-fused protein for the studies of protein—protein interactions. The reversible surface functionalization method has been proven by analytical techniques, fluorescence imaging, atomic force microscopic imaging, and electrical measurements. The reversible GSH—GST functionality on the SiNW-FET has made this sensorial device consecutively reusable and calibratable, allowing for quantitative analysis. In this work, we have demonstrated that the biologically modified SiNW-FET can be used as a screening sensor for the future studies of biomolecular associations, such as protein—protein interactions, protein—DNA interactions, protein—carbohydrate interactions, etc.

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Miniaturized biological sensors made of nanotube/nanowire field-effect transistors (NT/NW-FET) recently have attracted wide attention because of their high selectivity, extreme sensitivity, rapid response, and potential for integration into full electronic on-chip systems for high-throughput analysis [1–3]. A particular advantage of employing NT/NW-FET biosensors is their capability of in situ and real-time recording the signal changes caused by single cells and individual neurons [4,5]. NT/NW-FET can be massively produced and are relatively cost-effective in requiring less amount of sample than other large-scale biosensors [6,7]. Several applications of surface-functionalized NT/NW-FET have been reported for the detections of ions [8], DNA [9–11], proteins [12–19], glucose and hydrogen peroxide [8,20], and viruses [4].

In the current applications of NT/NW-FET for biomedical diagnosis of a particular antigen (target molecule), the corresponding antibody (probe molecule) is usually modified on the surfaces of NT/NW-FET prior to the detection. By virtue of the strong and specific binding affinity between antigen and antibody under a normal physiological condition, the surface-modified NT/NW-FET can serve as an extremely sensitive sensor with high selectivity. By the same token, because of this strong binding between antigen and antibody, it is difficult to remove the antigen-antibody complex from the surface of NT/NW-FET in the end of detection, yielding that a NT/NW-FET could be used just for a single measurement. With this limitation, consecutively quantitative analysis by a calibratable NT/NW-FET has been problematic to achieve.

Here, we report a novel strategy to design a reusable sensor by judiciously selecting a reversible association–dissociation molecular system to be functionalized on the surface of silicon nanowire field-effect transistor (SiNW-FET). It is well studied that protein fused with glutathione S-transferase (GST) can associate with glutathione (GSH)-conjugated resin for purification or studying protein–protein interaction [7,21,22]. GST binds GSH specifically with high affinity and the associated GST-fused protein can be eluted easily by a high concentration of GSH [23]. However, the traditional approach requires a large amount of proteins and tedious process. In this study, we chose GSH to be immobilized on a SiNW-FET (termed GSH/SiNW-FET), which can then anchor a specific protein fused with GST (termed protein–GST/GSH/SiNW-FET) to screen possible interacting proteins. Particular emphasis will be given to the reversible surface functionalization on the sensorial SiNW-FET. A schematic diagram for this retrieval surface-modified SiNW-FET is illustrated in Fig. 1 including the association of a GST-fused protein on a GSH/SiNW-FET to screen possible interacting proteins, the dissociation of the used GST-fused protein after detection, and the iterative retrievable cycles. In the pursuit of a fast high-throughput screening method, a myriad of protein–protein interactions can be examined by this protein–GST/GSH/SiNW-FET, where various GST-fused proteins can be easily prepared in a large scale via bacterial or mammalian expression systems [7,24,25].

In the immobilization of GSH on a SiNW-FET, a self-assembled monolayer (SAM) of 3-aminopropyltrimethoxysilane (APTMS) was first bonded to the silicon-oxide sheath on the SiNW. This SAM technique has been proven to be one of the most popular methods for the surface functionalization of devices [1,2,26,27]. A linker of 3-maleimidobenzoic acid N-hydroxysuccinimide ester (MBS) was then applied to bond APTMS on one end and to anchor GSH on the other end (Fig. 1). The GSH/SiNW-FET could subsequently be used for protein sensing experiments by anchoring a specific protein. To examine each-step modification on a Si substrate, we identified the elemental compositions and chemical-structure characteristics by electron spectroscopy for chemical analysis (ESCA), including APTMS anchoring, MBS linking, GSH immobilization, and GST association. The ESCA spectra in Fig. 2 show the spe-

Figure 1  Schematic illustration for the reversible functionalization of protein-GST on a GSH/SiNW-FET for rapid high-throughput screening protein interactions. A SiNW-FET is first modified with APTMS and MBS linkers prior to the immobilization of GSH. A particular protein-GST is then associated with the GSH/SiNW-FET for screening possible interacting proteins. In the end of each measurement, the used protein-GSTs are removed with 10 mM GSH washing solution, making the GSH/SiNW-FET a reusable biosensor.
Figure 2  The observed (a) C 1s and (b) N 1s ESCA spectra to examine the serial surface modification steps of (A) a clean Si substrate, (B) the modification of APTMS, (C) the insertion of an MBS linker, (D) the immobilization of GSH, and (E) the association with GST. The characteristic functional groups responsible for particular ESCA signals are identified. In the C 1s spectra, 1: Si–C, 2: C–C, 3: C–NH₂, 4: CONH, 5: C–O in C₁₁H₅NO₃, and 6: COOH. In the N 1s spectra, a: C–NH₂, b: CONH, and c: C₁₁H₅NO₃.

cific functional groups of the added molecule in each-step modification. For example, after an APTMS-SAM is anchored on the Si surface via silanol group, the spectral features in the C 1s ESCA spectrum (the B panel in Fig. 2a) are observed at 283.3, 285.0, and 286.6 eV corresponding, respectively, to the silicon carbide (Si–C), carbon–carbon (C–C), and amine (C–NH₂) groups of APTMS. Because of the coupling of MBS with APTMS, the specific peaks appear at 287.8 eV (amide) and 288.7 eV (C=O in maleimidobenzoyl) in the C 1s spectrum (the C panel in Fig. 2a). Meanwhile, a significant increase of two new peaks at 399.3 eV (amide) and 402.0 eV (maleimidobenzoyl) in the N 1s spectrum (the C panel in Fig. 2b) has also evidenced the existence of MBS. Owing to the very weak ESCA feature for the S element, we have chosen the carboxylic acid and amide groups as spectral indicators to demonstrate the presences of GSH and GST. In the D and E panels of Fig. 2a, the carboxyl groups of both GSH and GST are responsible for the peak at 289.0 eV. Furthermore, apparent increases of the amide group in the C 1s (287.8 eV) and N 1s (399.3 eV) spectra were observed after the association of GST with the GSH-modified Si substrate. Except the S element, the relative atomic percentages among Si, O, C, and N analyzed from the ESCA spectra for each-step modification are listed in Table 1. Before any surface functionalization, the main compositions of a Si substrate have the Si/O ratio of 32.3/67.7. After the APTMS modification, while the relative contents for both Si and O decrease, two additional elements of C and N appear in the ESCA spectra. Consistent with a previous report [28], the changes in the atomic compositions of our ESCA data correctly reflect the immobilization of APTMS on the Si surface. Table 2 lists the compositions of amine (C–NH₂), amide (CONH), and maleimidobenzoyl (C₁₁H₅NO₃) groups for each-step modification calculated from the N 1s ESCA spectra (Fig. 2b). It is noteworthy that the percentage of amide reaches 44.4% after associating GST with GSH and decreases to 28.6% after removing GST by 10 mM GSH. In comparison with the original 29.7% of amide in a GSH-modified Si substrate, this ESCA examination has indicated a thorough removal of GST by 10 mM GSH, demonstrating that the reversible GSH–GST association–dissociation is a suitable molecular system to be adapted for a reusable SiNW-FET sensor.

Table 1  ESCA analysis for the atomic compositions in each-step surface modification on a Si substrate. Results represent the mean ± SEM of readings obtained from four samples.

<table>
<thead>
<tr>
<th>Atomic composition (%)</th>
<th>Si</th>
<th>O</th>
<th>C</th>
<th>N</th>
</tr>
</thead>
<tbody>
<tr>
<td>Si substrate</td>
<td>32.3 ± 0.3</td>
<td>67.7 ± 0.7</td>
<td>—</td>
<td>—</td>
</tr>
<tr>
<td>APTMS–Si substrate</td>
<td>16.9 ± 0.4</td>
<td>25.9 ± 0.3</td>
<td>45.7 ± 0.8</td>
<td>11.5 ± 0.1</td>
</tr>
<tr>
<td>MBS–APTMS–Si substrate</td>
<td>13.0 ± 0.2</td>
<td>26.9 ± 0.4</td>
<td>47.7 ± 0.3</td>
<td>12.4 ± 0.5</td>
</tr>
<tr>
<td>GSH–MBS–APTMS–Si substrate</td>
<td>10.0 ± 0.4</td>
<td>27.2 ± 0.5</td>
<td>49.8 ± 0.2</td>
<td>13.0 ± 0.6</td>
</tr>
<tr>
<td>GST–GSH–MBS–APTMS–Si substrate</td>
<td>5.3 ± 0.4</td>
<td>29.6 ± 0.2</td>
<td>50.7 ± 0.5</td>
<td>14.4 ± 0.3</td>
</tr>
</tbody>
</table>
Table 2 The compositions of amine, amide, and maleimidobenzoyl groups in each-step surface modification on a Si substrate analyzed from the observed ESCA N 1s spectra.

<table>
<thead>
<tr>
<th>Si substrate</th>
<th>N-containing group composition (%)</th>
</tr>
</thead>
<tbody>
<tr>
<td>Amine (C—NH₂)</td>
<td>Amide (CONH)</td>
</tr>
<tr>
<td>APTMS—Si substrate</td>
<td>100</td>
</tr>
<tr>
<td>MBS—APTMS—Si substrate</td>
<td>49.5</td>
</tr>
<tr>
<td>GSH—MBS—APTMS—Si substrate</td>
<td>47.2</td>
</tr>
<tr>
<td>GST—GSH—MBS—APTMS—Si substrate</td>
<td>50.8</td>
</tr>
<tr>
<td>After 10 mM GSH washing the GST—GSH—MBS—APTMS—Si substrate</td>
<td>49.2</td>
</tr>
</tbody>
</table>

experiments, we have been able to conduct repeatedly the association–dissociation cycles of GST on a GSH-modified Si substrate for more than 30 times. Shown in Fig. 3a is the N 1s ESCA spectrum of a GSH-modified Si substrate after 30 cycles of the GSH–GST association–dissociation, which is noted to have the same pattern as the original GSH-modified Si substrate (the panel D in Fig. 2b).

Since fluorescent images can provide visual evidence of efficient surface modification [11,14,17,26], we have applied a microscopic fluorescence imaging technique to further demonstrate the antibody against GST and fluorescein isothiocyanate-labeled secondary antibody against primary antibody (termed FITC-aGST/GST) on a GSH-modified Si substrate and the thorough removal of FITC-aGST/GST by 10 mM GSH washing solution. In the fluorescence imaging examination of the surface modification, a micropattern was fabricated on a Si substrate with a standard photolithographic procedure using an SU-8 photoresist. The modification procedures of GSH and GST on the Si surface are the same as those described in the above ESCA spectroscopic examination (details in Supplementary Information (SI)). Fig. 3b shows the green fluorescence after the association of FITC-aGST/GST on a GSH-modified substrate. In comparison, Fig. 3c–e shows three negative controls with no fluorescence, because the FITC-aGST/GST could not be effectively associated on the Si substrate without an advanced immobilization of GST. To demonstrate that the associated FITC-aGST/GST could be removed thoroughly, the sample substrate was washed with 10 mM GSH for at least 5 min. As a result, the green fluorescence from FITC-aGST/GST (Fig. 3b) vanishes as displayed in Fig. 3f.

These successful surface functionalization procedures have been adapted to modify n-type SiNW-FETs in this study for real-time and label-free sensing experiments. The real-time conductance changes (ΔG) inside a GSH/SiNW-FET in response to the association and dissociation of GST are presented in Fig. 4a and b. In the electrical measurements, a polydimethylsiloxane (PDMS) microfluidic channel (6.25 mm × 0.5 mm × 0.05 mm) [29], aligned to couple with the SiNW-FET arrays, was designed to deliver a sample solution to the location of the SiNW-FET arrays by a syringe pump at a flow rate of 0.3 mL h⁻¹. It is noted in FET sensing experiments that an electric-field screening caused by the electrolytic environment is crucial for the detection sensitivity of an FET sensor. In this study, we dissolved samples, such as GST and GSH, in either phosphate buffered saline (1 x PBS, 137 mM NaCl, 2.7 mM KCl, 10 mM Na₂HPO₄, 2 mM KH₂PO₄, pH 7.4 with NaOH) or phosphate solution (1 x PS, 2.4 mM NaH₂PO₄, 7.6 mM Na₂HPO₄, pH 7.4 with NaOH) of different concentrations, thus with different Debye–Hückel screening lengths (λD). It is well known that biomolecules keep their characteristics from denaturing in a normal physiological condition (1 x PBS). However, the short λD ~ 0.8 nm for the ~0.14 nm biological electrolyte renders a severe screening effect in the sensing measurement, therefore deteriorating the detection sensitivity of the FET sensor [6,30,31]. In Fig. 4a, we observed that the electrical measurement of 15 nM GST by a GSH/SiNW-FET in either 0.1 x PBS (black curve) or 1 x PS (red curve) are about the same, where λD ~ 2 nm has been calculated for both of environmental electrolytes. Shown in Fig. 4b are the electrical measurements of 15 nM GST in further diluted 0.01 x PBS (black curve) or 0.1 x PS (red curve), where the measured results are also of no significant difference in either solution except a fourfold enhancement in the ΔG, compared with those in Fig. 4a, due to the longer λD ~ 6.6 nm in these diluted electrolytes. In view of the similar electric responses, both PBS and PS buffer solutions with the same λD should possess equal buffer ability for GSH and GST without altering their expressions during the measurements. The decreases of the conductance in the n-type SiNW-FET device after adding GST is caused by a gating effect because of the negatively charged GST (p1 ~ 6.72) at pH 7.4. In line of the same reasoning, the conductance returned to the initial level after the removal of GST with 10 mM GSH washing solution, also indicating a complete retrieval of the GSH/SiNW-FET as demonstrated in the two repeated cycles in Fig. 4a and b. These repeated cycles for the association and dissociation of GST on the GSH/SiNW-FET have been tested comprehensively in our experiments with one example of six consecutive retrieval cycles being provided in Fig. S1 of SI.

In a parallel examination to evidence the association and dissociation of GST on a GSH/SiNW-FET, we scanned the surface topographs of the SiNW-FET before and after the electrical measurements by atomic force microscopy (AFM). Prior to the surface modification, the top-view and profile AFM images of an unmodified SiNW-FET are displayed in Fig. 4c and d, respectively. After an electrical measurement, the association of GST on the GSH/SiNW-FET is clearly seen from the lumpy AFM image of Fig. 4e. It is noted that before the AFM imaging, the substrate of GST/GSH/SiNW-FET was washed for 15 min in vigorously stirred deionized water assisted by a mechanical rotator. The illustrative AFM image of Fig. 4e for the association of GST on GSH/SiNW-
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Figure 3  Demonstrations of the reversible association–dissociation of GST on a GSH modified Si substrate. (a) An N 1s ESCA spectrum obtained for a GSH modified Si substrate after 30 cycles of the GSH–GST association–dissociation, which has the same pattern as the original GSH-modified Si substrate (the panel D in Fig. 2(b)). (b) A microscopic fluorescence image of FITC-aGST/GST in association with a GSH immobilized Si substrate via the linkers of MBS and APTMS (termed FITC-aGST/GST/GSH/MBS/APTMS). The micropattern was fabricated with a standard photolithographic procedure. (c–e) Negative control tests show that FITC-aGST/GST could not be effectively associated on the Si substrate without an advanced immobilization of GSH. The surface modifications were (c) FITC-aGST/GST, (d) FITC-aGST/GST/APTMS, and (e) FITC-aGST/GST/MBS/APTMS. (f) The green fluorescence of FITC-aGST/GST in (b) vanishes after the sample substrate was washed with 10 mM GSH.

FET also illuminates the strong GSH–GST interaction. The effective removal of GST by 10 mM GSH washing is confirmed by the clean surface topograph of the SiNW-FET device in Fig. 4f.

In the electrical measurements with the SiNW-FET arrays immersed in solution, we found that the devices were easier contaminated by salts due to the more complex compositions in PBS than those in PS. We therefore dissolved biological samples in 0.1× PS (λD = 6.6 nm) in the following protein sensing experiments. The protein-binding selectivity of a GSH/SiNW-FET was tested by choosing avidin (pI ∼ 10.5) as a negative control. In Fig. 5(a), after balanced with 0.1× PS, the GSH/SiNW-FET showed no significant ΔG to 15 nM avidin (positively charged at pH 7.4), thus manifesting the binding specificity of the GSH/SiNW-FET. On the contrary, a substantial ΔG was monitored when 15 nM GST reached the GSH/SiNW-FET sensor. In total, we have measured the ΔG of GSH/SiNW-FET in response to various concentrations (2, 3, 6, 15, 50, and 100 nM) of GST as plotted in Fig. 5(b) with a working concentration range before saturation spanning around 2–15 nM comparable to other biosensors for GST sensing [7].

We also applied the SiNW-FET sensor to quantitatively analyze protein–protein interactions by taking the well known biotin–streptavidin interaction as a demonstrative example. To this end, we first added biotin-tagged antibody against GST (termed biotin-aGST) to bind a GST/GSH/SiNW-FET (termed biotin-aGST/GST/GSH/SiNW-
Figure 4  Environmental electrolytes with different Debye–Hückel screening lengths and the AFM surface topographs of a SiNW-FET. Real-time electrical measurements of the association and dissociation of GST on a GSH/SiNW-FET in (a) 0.1× PBS (black curve) and 1× PS (red curve) of $\lambda_D = 2$ nm and (b) 0.01× PBS (black curve) and 0.1× PS (red curve) of $\lambda_D = 6.6$ nm. The (c) top-view and (d) profile images of an unmodified SiNW-FET scanned by AFM. The wire has width, length, and thickness of 200 nm, 6 $\mu$m, and 50 nm, respectively. (e) The lumpy AFM image evidences the association of GST with the GSH/SiNW-FET. (f) The effective removal of GST by 10 mM GSH washing is confirmed by the clean surface topograph of the SiNW-FET device.

The electric responses of biotin-aGST/GST/GSH/SiNW-FET upon adding 10 and 20 nM streptavidin, respectively, and the returns of the conductance level after 10 mM GSH washings are also displayed in Fig. 5(c). The variation of $\Delta G$ in the biotin-aGST/GST/GSH/SiNW-FET to streptavidin at 10, 20, 40, 100, and 200 nM are depicted in Fig. 5(b) with a working concentration range before saturation around 10–40 nM. The decrease of conductance in the n-type SiNW-FET after adding streptavidin (pI $\sim 5.5$—6.5) [32] is due to the gating effect caused by the negatively charged streptavidin at pH 7.4. From our measurements, the sensitivity of the biotin-aGST/GST/GSH/SiNW-FET to detect streptavidin in 0.1× PS ($\lambda_D = 6.6$ nm) could reach a value better than 10 nm, despite the quite long distance of $\sim 15$ nm from the biotin–streptavidin complex to the surface of SiNW-FET, encompassing five linkers of biotin-aGST, GST, GSH, MBS, and APTMS. Further improvement of the detection limit by diluting the buffer solution of 0.1× PS was not tested to prevent the proteins from denaturing.

The construction and expression of a GST-tagged protein are routine procedures in a molecular biology laboratory. Although the target protein expressed is amid many interfering molecules in the analyte, the tagged protein can be concentrated by several approaches, like fractionation and fast protein liquid chromatography, to increase its concentration so as to minimize the background. Furthermore, this expression can be conducted in a cell-free in vitro system with high yield and low background interference [33].

Without the reversible surface functionalization, a tedious surface modification process has to be carried out for each individual chip, and device-to-device variations in the number of probe molecules modified on an FET sensor would cause uncertainty in quantitative analysis. Since the reversible functionalization process does not change the number of GST molecules on the GSH/SiNW-FET, it provides an economic and convenient approach for quantitative analyses. Although the probe–nanowire distance was increased $\sim 6$ nm by the GSH–GST molecule chain, thus decreasing the sensitivity of the device, our current design could still respond to the protein–protein interaction with high sensitivity. This, together with the reusability, makes the proposed technology well suited for biosensor researches.

In conclusion, we have demonstrated a novel method by imparting the reversible functionality of GSH–GST on the surface of SiNW-FETs to make the sensor reusable. The surface functionalizations on Si substrates were confirmed by ESCA and fluorescent imaging in all modification steps, including APTMS anchoring, MBS linking, GSH immobilization, and GST association. Removal of the associated GST from GSH/SiNW-FET with 10 mM GSH was verified by AFM imaging. The reversible functionalization of GST on the GSH/SiNW-FET has made this sensorial device consecutively reusable and calibratable, allowing for quantitative analysis. The detection of streptavidin by the biotin-aGST/GST/GSH/SiNW-FET in the concentration range of 10–200 nM has demonstrated this biologically modi-
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Figure 5

Protein sensing and detection limit. (a) In the specific recognition of GST, a prominent $\Delta G$ in a GSH/SiNW-FET is monitored, which is in contrast to no clear electric response in the detection of avidin as a negative control test. (b) The $\Delta G$ of a GSH/SiNW-FET in the detections of GST for various analyte concentrations (red curve) and the $\Delta G$ of biotin-aGST/GST/GSH/SiNW-FET to streptavidin (blue curve). Each data point represents the mean $\pm$ SEM from four measurements. (c) Real-time detections of the binding of biotin-aGST to GST/GSH/SiNW-FET and the subsequent sensing of streptavidin. All measurements were carried out in 0.1 x PS of $\lambda_0 = 6.6$ nm.

Acknowledgments

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Appendix A. Supplementary data

Supplementary data associated with this article can be found, in the online version, at doi:10.1016/j.nantod.2009.04.005.

References

Shu-Ping Lin received her B.S. and M.S. degrees in Biomedical Engineering at Chung-Yuan Christian University in 2001 and 2003, respectively. In 2008, she obtained her Ph.D. degree in Biomedical Engineering from National Cheng-Kung University. She was a visiting graduate fellow in Dr. Themis Kyriakides’s laboratory at Yale University from 2006 to 2007 to carry out part of her Ph.D. thesis research on 3D cells growth on surface-modified biosensors. In 2008, she worked as a postdoctoral researcher at Institute of Atomic and Molecular Sciences, Academia Sinica, Taiwan. Her research interests are mainly directed toward designing and developing biocompatible biosensors, biomaterials syntheses and analyses, and impedance evaluation of cell electrical property.

Chien-Yuan Pan is currently an associate professor at Institute of Zoology, National Taiwan University, Taipei, Taiwan. He received his B.S. degree from Department of Chemistry, National Taiwan University. When he was an undergraduate, he was fascinated with mountain-climbing and exploring the wild mountain area in Taiwan. After 2-year service in the Army, he had his Ph.D. training under Prof. Lung-Sen Kao at Institute of Biochemistry, National Yang-Ming University, Taipei, Taiwan. He then worked with Prof. Aaron Fox in University of Chicago as a postdoctoral fellow for 4 years. In 2002, he got this faculty job in National Taiwan University. His research is now focused on the stimulus-secretion coupling and $\text{Ca}^{2+}$ homeostasis in the neuronal cells using electrophysiological patch clamping and $\text{Ca}^{2+}$ fluorimetry techniques.

Kun-Chang Tseng was born in Taiwan in 1983. He received his B.S. degree in Chemistry from National Central University in 2005. Since 2007, he has been a graduate student in Department of Chemistry at National Taiwan University under the supervision of Prof. Yit-Tsong Chen. His research is focused on the new applications of silicon nanowire field-effect transistor, the reusability of biosensor, and the development of high-throughput protein screening platform.

Ming-Chou Lin received his B.S. and M.S. degrees in physics from Fu-Jen Catholic University in 2001 and National Chung-Cheng University in 2003, respectively. Currently, he is a 4th-year Ph.D. student in Graduate Institute of Electronics Engineering and Department of Electrical Engineering at National Taiwan University. His research focuses on the fundamentals and applications of silicon quantum-dot single-electron-transistors and silicon nanowire field-effect-transistors.

Chii-Dong Chen is a research fellow at Institute of Physics, Academia Sinica, Taipei, Taiwan. He joined the faculty in 1997 after receiving a B.S. degree from Nation Cheng-Kung University (where he is now a joint Professor), Tainan, Taiwan, a M.E. degree from Tokyo Institute of Technology, Tokyo, Japan, a Ph.D. degree from Chalmers University of Technology, Gothenburg, Sweden and a NEDO postdoctoral fellowship in NEC Fundamental Research Laboratory, Tsukuba, Japan. His fields of experience are fabrication and characterization of nano-devices and his research interests include fundamental transport physics as well as applications of quantum electronics.

Chia-Chang Tsai was born in Ping-Tung, Taiwan in 1976. He received his B.S. degree in Physics from Chung-Hsing University (1998), and Ph.D. degree in Physics from Cheng-Kung University (2005). He is now a postdoctoral fellow at Institute of Atomic and Molecular Sciences, Academia Sinica, Taiwan. His current research interests focus on nanotechnology and biochemical physics.

Shu-Han Yu was born in Chia-Yi, Taiwan in 1980. He received his B.S. degree in Chemistry (2005) from SooChow University and M.S. degree in Chemistry (2008) from National Taiwan Normal University. His research is focused on the synthesis and characterization of silicon nanowires, and the detection of protein-protein interactions by silicon nanowire field-effect transistor.

Ying-Chieh Sun is a professor at Chemistry Department of National Taiwan Normal University. He received his B.S. degree in Chemistry from National Taiwan University in 1987, and Ph.D. degree from Chemistry Department at University of Pennsylvania, USA in 1994, working on hydrogen dynamics on surface. He was a postdoctoral fellow at Department of Pharmaceutical Chemistry, University of California, San Francisco, working on protein stability. He started his faculty...
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Yit-Tsong Chen is a professor at Chemistry Department of National Taiwan University. He is also an adjunct Research Fellow at Institute of Atomic and Molecular Sciences, Academia Sinica in Taiwan. He joined the faculties in 1991 after receiving his B.S. degree from National Taiwan University (1980) and Ph.D. degree from University of Chicago (1988), and having postdoctoral research training at MIT (1989–1991). In his early research career, he was interested in the studies of superfine structures, vibrational dynamics, and Rydberg states of fundamental molecules using a variety of nonlinear laser optics. In the late 1990s, fascinated by the nanoscale world, he shifted part of his research on catalytic growth and spectroscopic characterization of nanoparticles and nanowires. His current interests are focused on applying field-effect transistor, scanning probe microscopy, and optical microscopy as biosensors to study protein–protein interaction, extracellular ionic fluctuation, cellular exo-endocytosis, and neuron–neuron interaction.

Tsung-Wu Lin was born in Taiwan in 1976. He received his M.S. degree in Chemistry from National Tsing-Hua University, Taiwan and Ph.D. degree from University of Oxford, UK in 2007. He is currently a postdoctoral fellow at Institute of Atomic and Molecular Sciences, Academia Sinica, Taiwan. His research interests are the application of nanomaterials in the drug delivery and the use of silicon nanowire field-effect transistor for biosensing.

job in 1996 at the current department, mainly working on the computational chemistry/structural biology area, including TiO$_2$ nanoparticle surface and protein/peptide dynamics. His current interests are protein–ligand interaction, drug discovery/design, and cell biology.

T sung-Wu Lin was born in T aiwan in 1976. He received his M.S. degree in Chemistry from National T sing-Hua University, T aiwan and Ph.D. degree from University of Oxford, UK in 2007. He is currently a postdoctoral fellow at Institute of Atomic and Molecu-lar Sciences, Academia Sinica, T aiwan. His research interests are protein—ligand interaction, drug discovery/design, and cell biology.
1. Experimental details

1.1. Fabrication of SiNW-FET

Four-inch silicon-on-insulator (SOI) wafers with a 50 nm thick Si top layer and a 400 nm thick buried oxide layer were used in this work. The typical resistivity of the device layer is 100 Ω·cm. The lithographic procedures to fabricate SiNW-FET on SOI are similar to those described in our previous publication [1]. The nanowires were defined by standard electron beam lithography and a dry-etching process in an inductively-coupled-plasma etcher with C₄F₈ and SF₆ gas mixture. The as-fabricated nanowires were thermally oxidized at 900 °C for 20 min in an O₂ ambient to form a 10 nm thick SiO₂ insulating layer to inhibit any charge transfer between the wires and surrounding molecules in the sensing experiments. The nanowires were then connected to the outside millimeter-size contact pads via heavily boron-doped micrometer-wide Si leads patterned by photolithography. The ion implantation was carried out with a nominal doping concentration of 10¹⁹ cm⁻³ at an implantation energy of 11 keV which gave a doping depth of ~40 nm. The implanted ions were activated by annealing at 950 °C for 20 min in an N₂ ambient. Finally, the contact pads were covered by a 50 nm thick Au film and a 10 nm thick Ni buffer layer.

1.2. Surface modification and characterization

Before surface modification, the organic contaminants on the Si chips (0.8×0.8 cm²) were first removed in an ethanol bath followed by washing in a solution containing 25% hydrogen peroxide and 75% sulfuric acid for 10 min. The APTMS-SAM was formed by immersing the chips (or SiNW-FETs)
in 1 mM ethanolic solution of APTMS (Fluka) for 1 h. After the immersion, the chips were carefully
rinsed with ethanol and then heated in ethanol in an oven at 60 °C for 5 min. The chips were further
rinsed with ethanol three times and blown dry with pure N₂ gas. Subsequently, the chips with an
APTMS-SAM were immersed for 2 h in 1 mM ethanolic solution of MBS (Sigma), which served as a
linker that can initially couple to molecules containing primary amines by amide bonds buffered at pH
7.0, followed by coupling to compounds containing sulfhydryl by thioether at the same pH [2]. The
chips were rinsed again with ethanol three times and blown dry with pure N₂ gas. The immobilization
of GSH (Sigma) followed by the modifications of APTMS and MBS was carried out in 1× PS at pH
7.0 for 2 h. The association of GST (Sigma) with a GSH-modified chip was conducted in 1× PS at pH
7.4 for 1 h.

The elemental compositions and chemical-structure characteristics of the anchored molecules in
each-step modification were examined by ESCA. The ESCA spectra were acquired with a Sigma
Probe (Thermo VG-Scientific) and a micro-focus monochromatic aluminum anode X-ray at 108 W,
15 kV, and 10 mA (Al (Kα) 1253.6 eV, type 10-360 spherical capacitor analyzer). In the
determination of the elemental compositions, the C1s, O1s, N1s, and Si2p core level spectra were
measured and calculated from the ESCA peak area with correction algorithms and atomic sensitivity
factors (i.e. 1, 2.93, 1.8, and 0.817 for C1s, O1s, N1s, and Si2p, respectively) [3]. The spectra were
fitted using Voigt peak profiles and a Shirley background [4] together with a database for
semiconductor [5] and organic polymers [6].

The fluorescence images of the surface-modified micropatterns on the chips were photographed
in a phase-contrast upright fluorescence microscope (Zeiss, Axioplan 2 Imaging MOT) equipped with
an intensified Cool Snap EZ charged coupled device camera. The stained chips were incubated in 1%
bovine serum albumin (BSA) 1× PS containing primary mouse monoclonal IgG against GST (1:400,
GenScript) for 2 h at room temperature. The sample substrates were washed with 1× PS 3 times, 5 min
for each. Subsequently, the sample substrates were incubated with secondary FITC-conjugated rabbit
antibody against mouse IgG (1:1000, Sigma) in 2% BSA 1× PS for 1 h. After washing with 1× PS 3 times, 5 min for each, the stained sample substrates were photographed with a fluorescence microscope.

1.3. Surface topograph of SiNW-FET

The surface topographs of SiNW-FET were scanned in air using an AFM (Digital Instruments, Bioscope SZ) based on an inverted optical microscope (Nikon, TE2000E). The AFM images of 512×256 pixels (512 line samples and 256 scan lines) were collected in tapping mode at a scanning frequency of 0.5 Hz, a resonant frequency of ~310 kHz, and the amplitude setpoint of ~0.6 V close to the target amplitude of 0.8 V. The integral and proportional gains of the scanning parameters are about 0.3 and 0.8, respectively. In the AFM imaging, the Si tips (Nanosensors, PPP-RT-NCHR-20) of a resonance frequency of ~204–497 kHz and a spring constant of ~10–130 Nm⁻¹ were used.

1.4. Electrical measurement

In the protein sensing experiments, the electric-conductance signals of SiNW-FET were measured at $V_{sd} = 30$ mV by a detection system combining a preamplifier (DL Instrument 1211) and a lock-in amplifier (Stanford Research System, SR830) with a modulation frequency of 17 Hz and a time constant of 100 ms. In the electrical measurements, a Ag/AgCl-electrode (BAS, MF2052) was applied to serve as a reference electrode. The sample solutions used in the protein sensing experiments, including avidin (15 nM, Sigma), anti-GST-tagged biotin (1:1000, Abcam), and streptavidin (10, 20, 40, 100, and 200 nM, Calbiochem) were prepared in 0.1× PS at pH 7.0.
2. The reversible association-dissociation of GST on a GSH/SiNW-FET

![Graph showing the iterative association-dissociation of GST on a GSH/SiNW-FET](image)

**Figure S1.** An example to demonstrate the iterative association-dissociation of GST on a GSH/SiNW-FET in six consecutive retrieval cycles. The electrical measurement was carried out in $0.1 \times$ PS of $\lambda_D = 6.6$ nm.

**References:**